

# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	Ic	600	mA

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_{D}$	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	625	°C/W
Operating and Storage and Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

## **Thermal Characteristic and Derating Information**

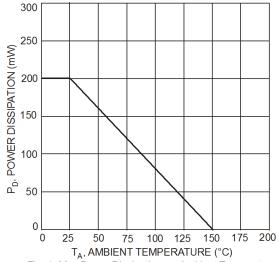


Fig. 1 Max Power Dissipation vs. Ambient Temperature

<sup>6.</sup> For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

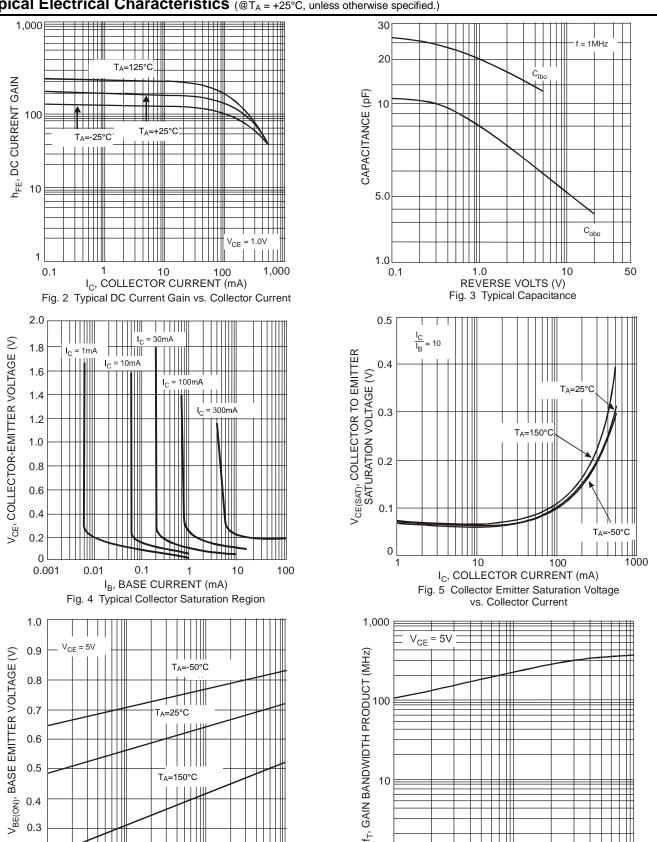
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60		V	$I_C = 100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 8)	BV <sub>CEO</sub>	40	_	V	$I_C = 10.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6.0	_	V	$I_E = 100 \mu A, I_C = 0$
Collector-Emitter Cut-Off Current	I <sub>CEX</sub>		100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$
Base Cut-Off Current	I <sub>BL</sub>		100	nA	$V_{CE} = 35V$ , $V_{EB(OFF)} = 0.4V$
ON CHARACTERISTICS (Note 8)					
DC Current Gain	h <sub>FE</sub>	20 40 80 100 40	  300 	_	$I_{C} = 100\mu A, V_{CE} = 1.0V$ $I_{C} = 1.0mA, V_{CE} = 1.0V$ $I_{C} = 10mA, V_{CE} = 1.0V$ $I_{C} = 150mA, V_{CE} = 1.0V$ $I_{C} = 500mA, V_{CE} = 2.0V$
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (SAT)	_	0.40 0.75	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.75	0.95 1.2	V	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_{obo}$	_	6.5	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	$C_{ibo}$	_	30	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_{C} = 0$
Input Impedance	h <sub>ie</sub>	1.0	15	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.1	8.0	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h <sub>fe</sub>	40	500	_	f = 1.0kHz
Output Admittance	h <sub>oe</sub>	1.0	30	μs	
Current Gain-Bandwidth Product	f⊤	250	_	MHz	$V_{CE} = 30V, I_{C} = 150mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>D</sub>	_	15	ns	$V_{CC} = 30V, I_C = 150mA,$
Rise Time	t <sub>R</sub>	_	20	ns	$V_{BE(OFF)} = 2.0V, I_{B1} = 15mA$
Storage Time	t <sub>S</sub>	_	225	ns	$V_{CC} = 30V, I_C = 150mA,$
Fall Time	t <sub>F</sub>	_	30	ns	$I_{B1} = -I_{B2} = 15\text{mA}$

Note:

8. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



 $\rm I_{C}$ , COLLECTOR CURRENT (mA)

Fig. 6 Base Emitter Voltage vs. Collector Current

0.2

100

10 I<sub>C</sub>, COLLECTOR CURRENT (mA)

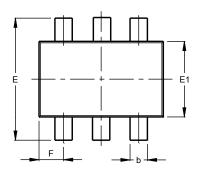
Fig. 7 Gain Bandwidth Product vs. Collector Current

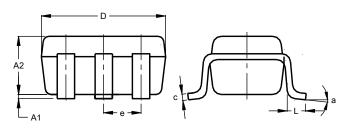


### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**



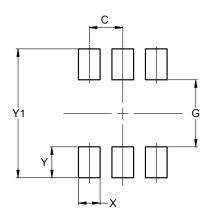


SOT363					
Dim	Min	Max	Тур		
A1	0.00	0.10	0.05		
A2	0.90	1.00	1.00		
b	0.10	0.30	0.25		
С	0.10	0.22	0.11		
D	1.80	2.20	2.15		
Е	2.00	2.20	2.10		
E1	1.15	1.35	1.30		
е	0.650 BSC				
F	0.40	0.45	0.425		
L	0.25	0.40	0.30		
а	0°	8°			
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500



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